Silicon PNP Power Transistors 2SB697 2SB697K

DESCRIPTION

·With TO-3 package
·Complement to type 2SD733/733K
·High power dissipation

APPLICATIONS

·Power amplifier applications
·Recommended for high-power high-fidelity audio frequency amplifier output stage

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SB697	Open emitter	-160	V
		2SB697K		-180	
V_{CEO}	Collector-emitter voltage	2SB697	Open base	-140	V
		2SB697K		-160	
V_{EBO}	Emitter-base voltage		Open collector	-6	V
I_C	Collector current			-12	A
I_{CM}	Collector current-peak			-20	A
P_C	Collector power dissipation		T_C=25□	100	W
T_j	Junction temperature			150	□
T_{stg}	Storage temperature			-40~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB697	I_C=-50mA ;I_B=0	-140			V
		2SB697K		-160			
$V_{(BR)CBO}$	Collector-emitter breakdown voltage	2SB697	I_C=-5mA ;I_E=0	-160			V
		2SB697K		-180			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=-5mA ;I_C=0	-6			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=-6A; I_B=-0.6A		-1.0	-2.5	V
V_{BE}	Base-emitter on voltage		I_C=-1A ; V_{CE}=-5V			-1.5	V
I_{CBO}	Collector cut-off current		V_{CB}=-80V; I_E=0			-0.1	mA
I_{EBO}	Emitter cut-off current		V_{EB}=-4V; I_C=0			-0.1	mA
h_{FE-1}	DC current gain		I_C=-1A ; V_{CE}=-5V	40		320	
h_{FE-2}	DC current gain		I_C=-5A ; V_{CE}=-5V	20			
f_T	Transition frequency		I_C=-1A ; V_{CE}=-5V		15		MHz

◆ **h_{FE-1} Classifications**

C	D	E	F
40-80	60-120	100-200	160-320

PACKAGE OUTLINE

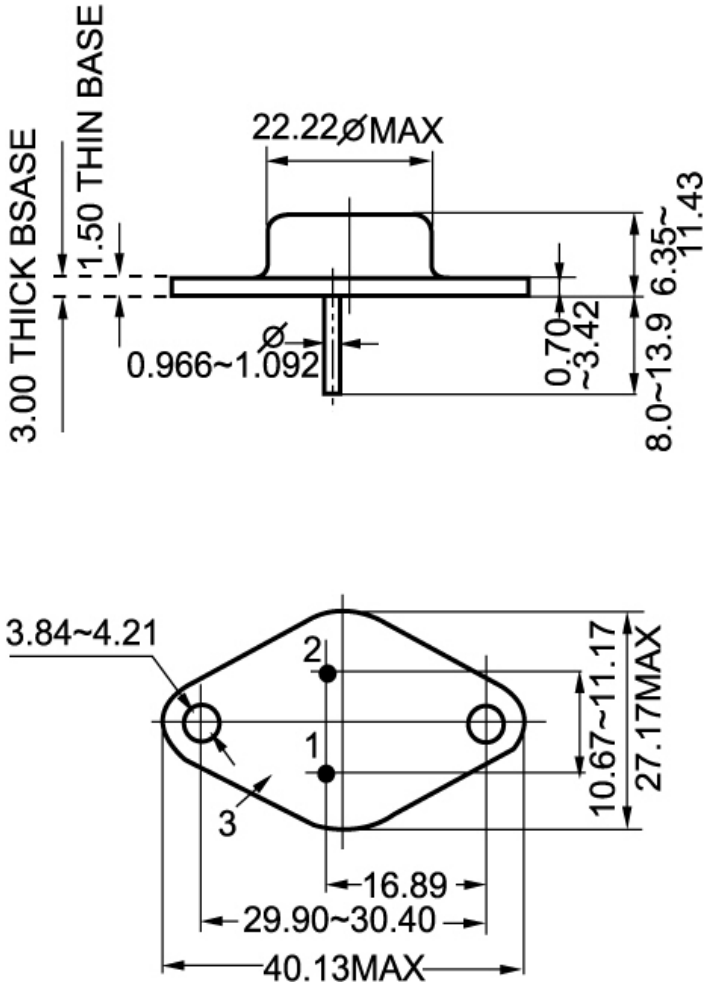

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)